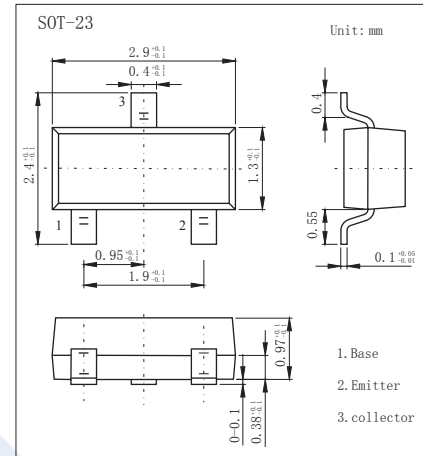


NPN Transistors

2SC2996

■ Features

- Collector Current Capability $I_c=50\text{mA}$
- Collector Emitter Voltage $V_{CE0}=30\text{V}$

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	40	V
Collector - Emitter Voltage	V_{CE0}	30	
Emitter - Base Voltage	V_{EB0}	4	
Collector Current - Continuous	I_c	50	mA
Emitter Current	I_E	-50	
Collector Power Dissipation	P_c	150	mW
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 125	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_c = 100 \mu\text{A}, I_E = 0$	40			V
Collector- emitter breakdown voltage	V_{CE0}	$I_c = 1\text{mA}, I_B = 0$	30			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100 \mu\text{A}, I_c = 0$	4			
Collector-base cut-off current	I_{CB0}	$V_{CB} = 40\text{V}, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = 4\text{V}, I_c = 0$			0.5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = 50\text{mA}, I_B = 5\text{mA}$			0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = 50\text{mA}, I_B = 5\text{mA}$			1.2	
DC current gain	h_{FE}	$V_{CE} = 6\text{V}, I_c = 1\text{mA}$	40		240	
Collector-base time constant	$C_{c\text{ rbb'}}$	$V_{CE} = 6\text{V}, I_E = -1\text{mA}, f = 30\text{MHz}$			30	ps
Noise figure	NF	$V_{CE} = 6\text{V}, I_E = -1\text{mA}, f = 100\text{MHz}$		4		dB
Power gain	PG			15		
Oscillation output voltage	V_{OSC}	$V_{CE} = 6\text{V}, f = 100\text{MHz}$		150		mV
Common emitter reverse transfer capacitance	C_{re}	$V_{CE} = 6\text{V}, f = 1\text{MHz}$			1.3	pF
Transition frequency	f_T	$V_{CE} = 6\text{V}, I_E = -1\text{mA}$	150			MHz

■ Classification of h_{FE}

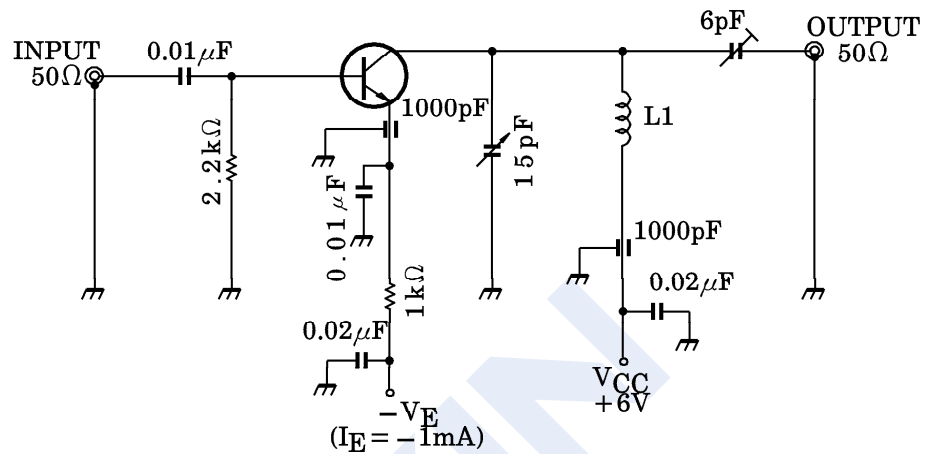
Type	2SC2996-R	2SC2996-O	2SC2996-Y
Range	40-80	70-140	120-240
Marking	GR	GO	GY

NPN Transistors

2SC2996

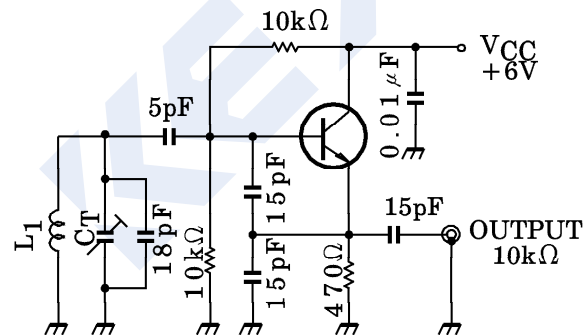
■ Typical Characteristics

Fig.1 NF, G_{pe} TEST CIRCUIT



L_1 : 0.8mm ϕ SILVER PLATED COPPER WIRE, 4T, 10ID, 8 LENGTH

Fig.2 V_{OSC} TEST CIRCUIT

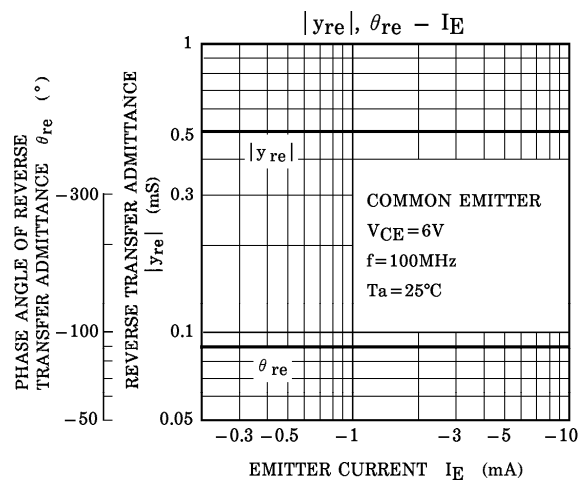
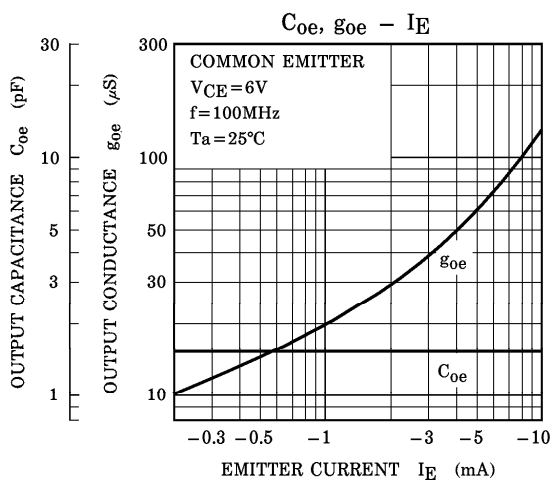
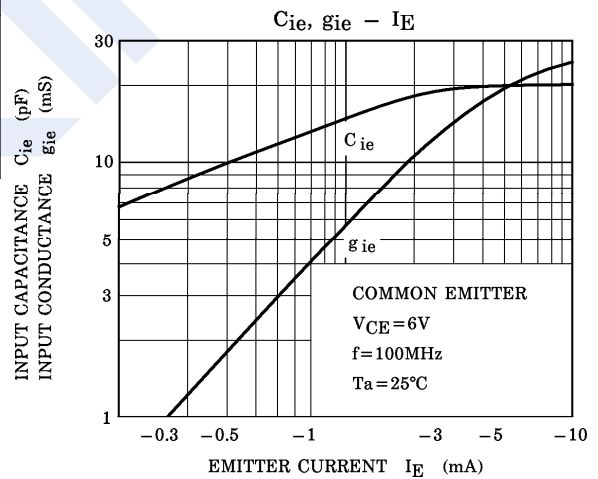
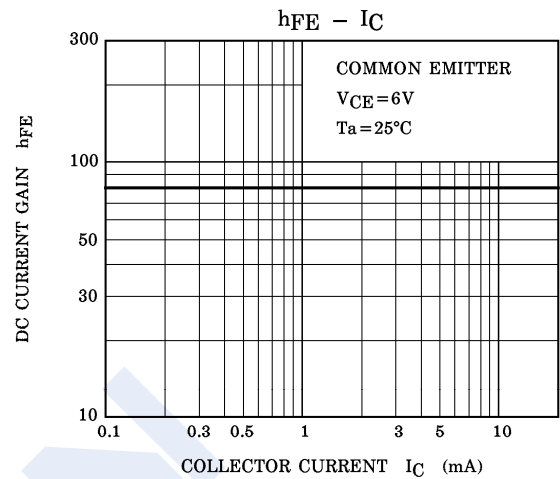
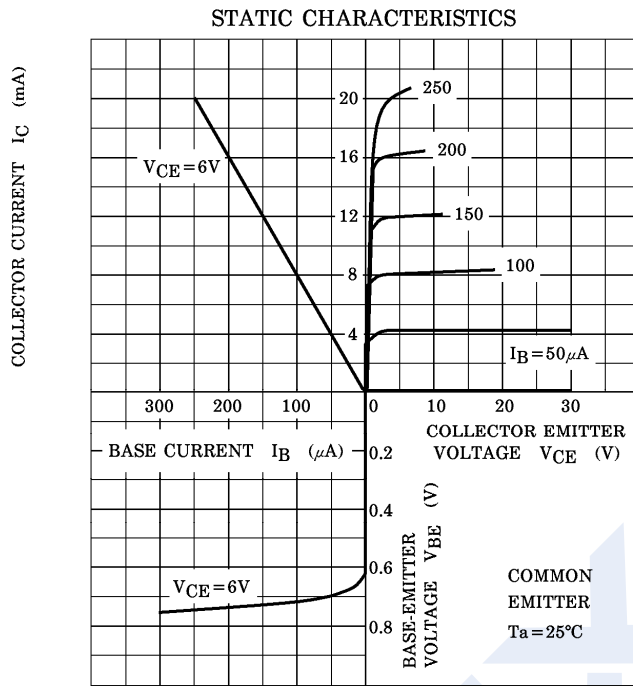


L_1 : 0.8mm ϕ SILVER PLATED COPPER WIRE, 4T, 10ID, 8 LENGTH

NPN Transistors

2SC2996

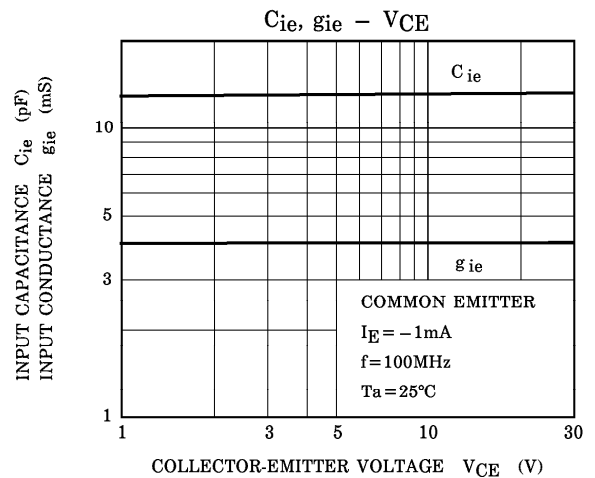
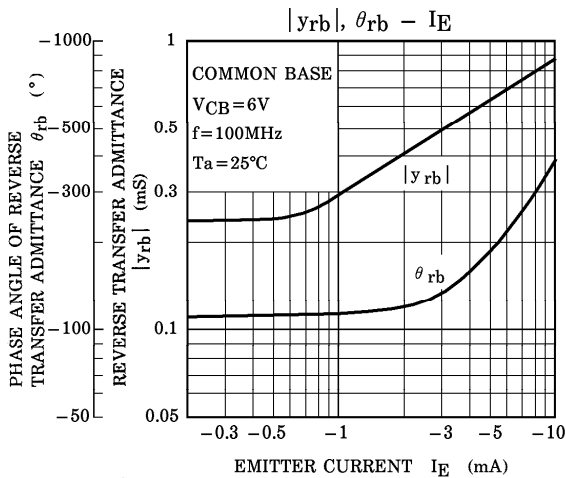
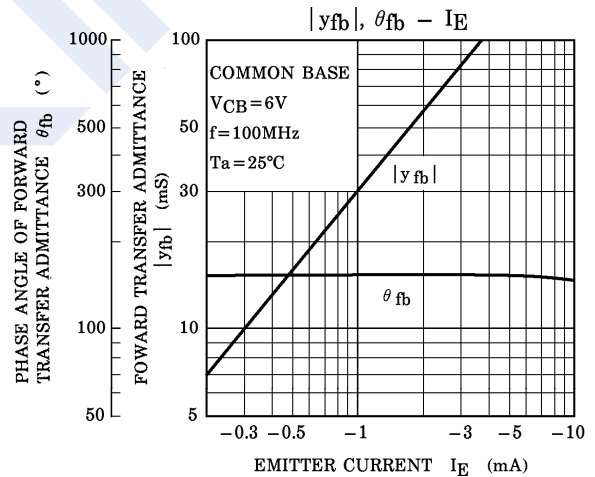
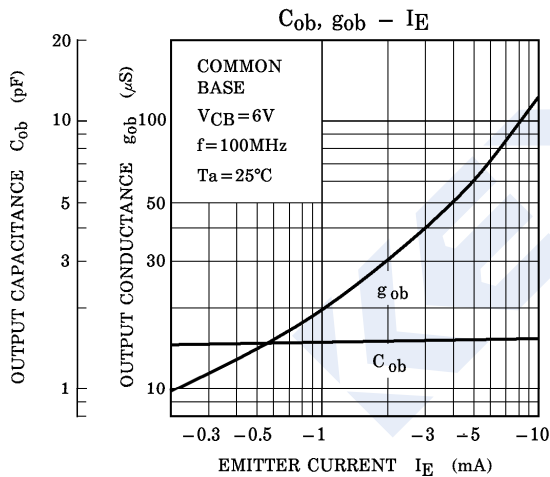
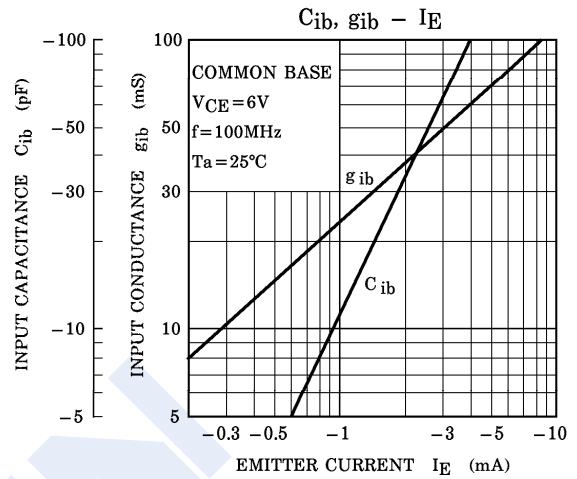
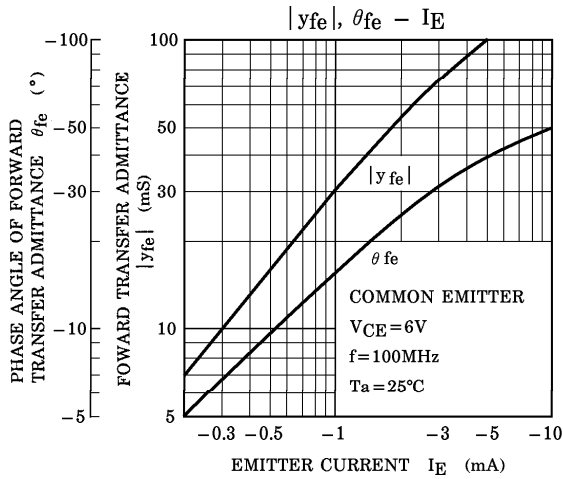
■ Typical Characteristics



NPN Transistors

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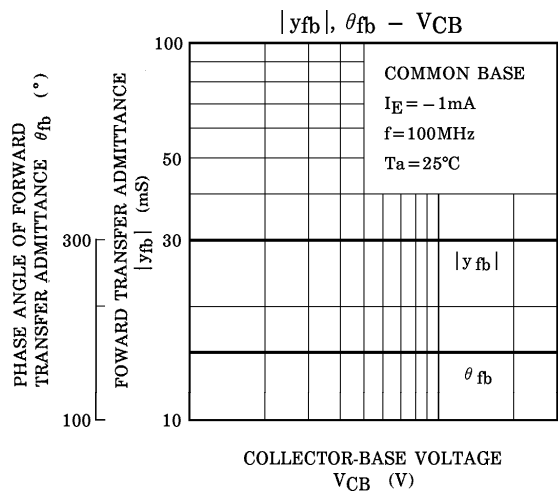
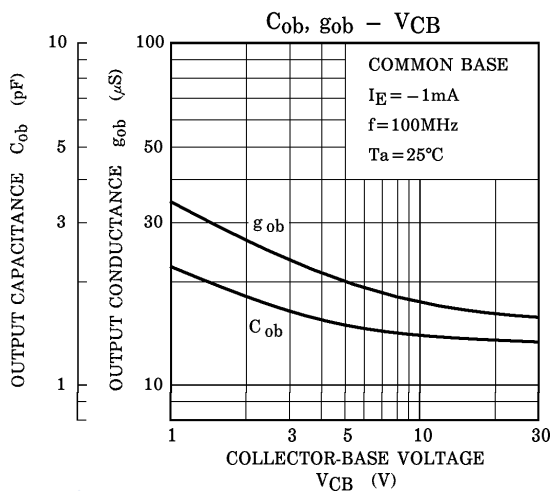
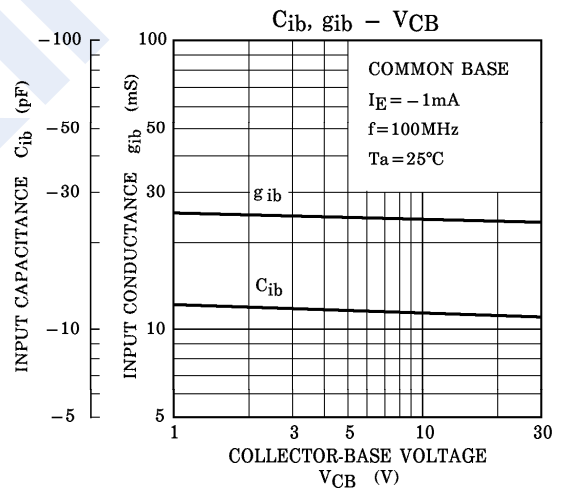
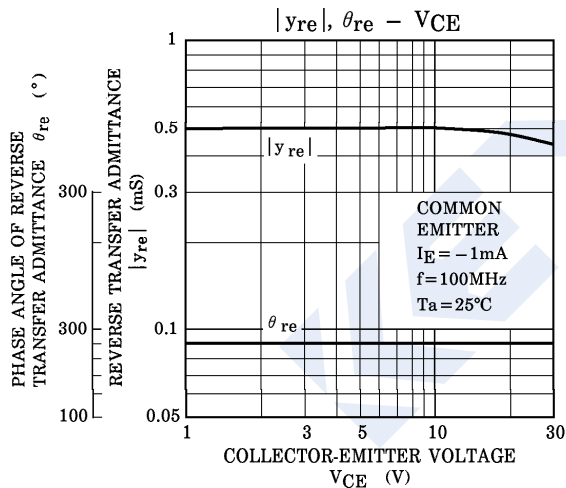
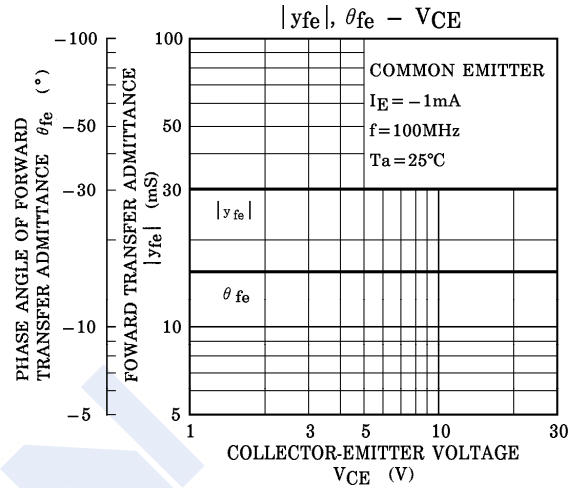
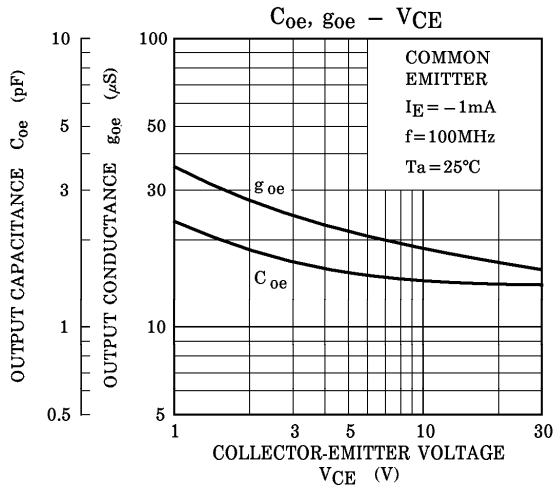
Typical Characteristics



NPN Transistors

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■ Typical Characteristics



NPN Transistors

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Typical Characteristics

